

PSMN2R9-25YLC

N-channel 25 V 3.15 m Ω logic level MOSFET in LFPAK using NextPower technology

Rev. 1 — 2 May 2011

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High reliability Power SO8 package, qualified to 175°C
- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD and QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Power OR-ing
- Server power supplies
- Sync rectifier

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	-	25	V
I_D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V;$ see Figure 1	<u>[1]</u> -	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	92	W
Tj	junction temperature		-55	-	175	°C



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12	-	3.45	4.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C};$ see Figure 12	-	2.65	3.15	mΩ
Dynamic c	haracteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 12 \text{ V};$	-	4.4	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	16	-	nC

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	S	source		_	
2	S	source	mb	D	
3	S	source		g (EA)	
4	G	gate	[q]		
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 S	
			SOT669 (LFPAK; Power-SO8)		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN2R9-25YLC	LFPAK; Power-SO8	plastic single-ended surface-mounted package; 4 leads	SOT669

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PSMN2R9-25YLC	2C925L

^[1] % = placeholder for manufacturing site code.

PSMN2R9-25YLC

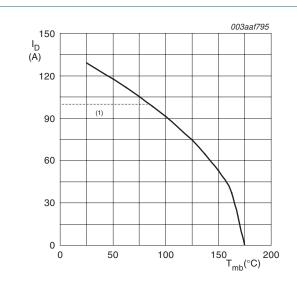
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

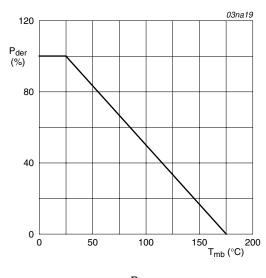
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	25	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	25	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u> -	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	91	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 4	-	517	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	92	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	380	-	V
Source-drain	n diode				
Is	source current	T _{mb} = 25 °C	-	83	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	517	Α
Avalanche re	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 25 V; unclamped; R_{GS} = 50 Ω; see Figure 3	-	47	mJ

^[1] Continuous current is limited by package.



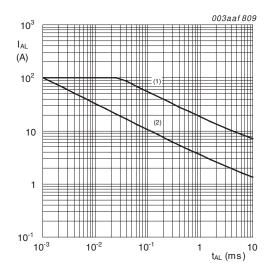
 $V_{GS} \ge 10V$; (1) Capped at 100A due to package

Fig 1. Continuous drain current as a function of mounting base temperature



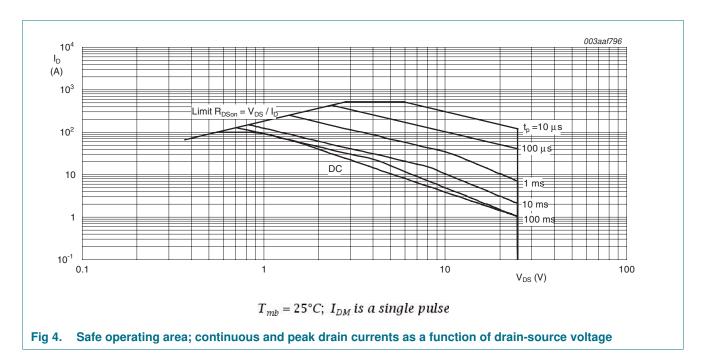
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

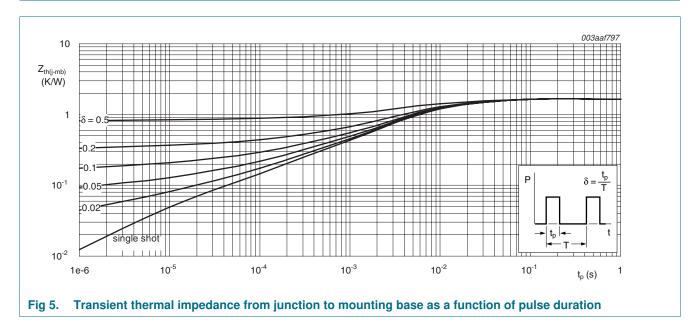
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	1.46	1.64	K/W



7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics	Conditions	B.41	Trees	Marr	11
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
	racteristics	L 050A. V 0.V.T 05.00	٥٢			V
V _{(BR)DSS} drain-source breakdown voltage		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	25	-	-	-
.,		$I_D = 250 \mu\text{A}; V_{GS} = 0 V; T_j = -55 ^{\circ}\text{C}$	22.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	1.05	1.54	1.95	V
		$I_D = 10 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C}$	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	2.25	V
I_{DSS}	drain leakage current	V_{DS} = 25 V; V_{GS} = 0 V; T_j = 25 °C	-	-	1	μΑ
		V_{DS} = 25 V; V_{GS} = 0 V; T_j = 150 °C	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12	-	3.45	4.1	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 150 \text{ °C};$ see Figure 12; see Figure 13	-	-	6.6	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 25 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 12	-	2.65	3.15	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 150 °C; see Figure 12; see Figure 13	-	-	5.05	mΩ
R _G	gate resistance	f = 1 MHz	-	2	4	Ω
Dynamic	characteristics					
Q _{G(tot)} total gate charg	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 12 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	33	-	nC
		I_D = 25 A; V_{DS} = 12 V; V_{GS} = 4.5 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	16	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	29	-	nC
Q _{GS}	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see Figure 14; see Figure 15	-	3.4	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	1.6	-	nC
Q_{GD}	gate-drain charge		-	4.4	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 12 V; see <u>Figure 14</u> ; see Figure 15	-	2.55	-	V
C _{iss}	input capacitance	V _{DS} = 12 V; V _{GS} = 0 V; f = 1 MHz;	-	2083	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	501	-	pF
C _{rss}	reverse transfer capacitance		-	160	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 4.5 \text{ V};$	-	19.5	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	19	-	ns
t _{d(off)}	turn-off delay time		_	32	_	ns
t _f	fall time		-	13	-	ns
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OIVIINEI 13-23 I LU		rai information provided in this document is subject to legal discidiffiers.		Nexpe	ria B.V. 2017.	All rights re

 Table 7.
 Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q_{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 12 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	18.5	-	nC
Source-drain diode						
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 17	-	8.0	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	32	-	ns
Q _r	recovered charge	V _{DS} = 12 V	-	23	-	nC
t _a	reverse recovery rise time	V_{GS} = 0 V; I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{DS} = 12 V; see <u>Figure 18</u>	-	18	-	ns
t _b	reverse recovery fall time		-	14	-	ns

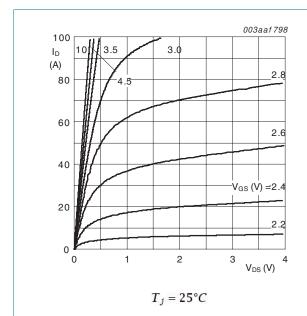


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

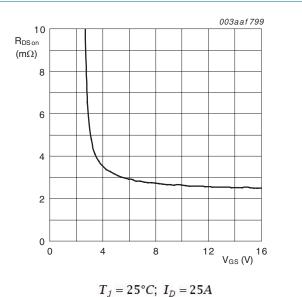


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

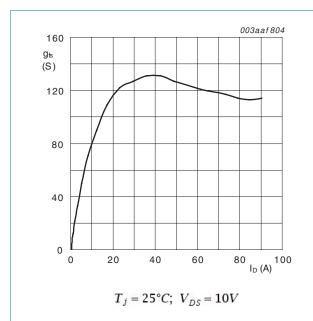


Fig 8. Forward transconductance as a function of drain current; typical values

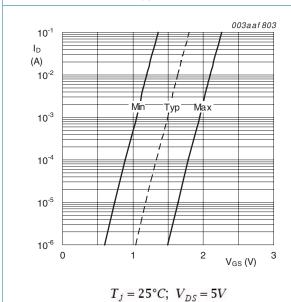


Fig 10. Sub-threshold drain current as a function of gate-source voltage

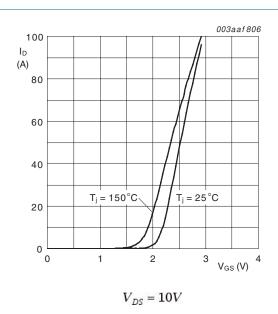


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

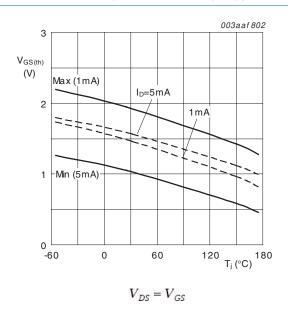


Fig 11. Gate-source threshold voltage as a function of junction temperature

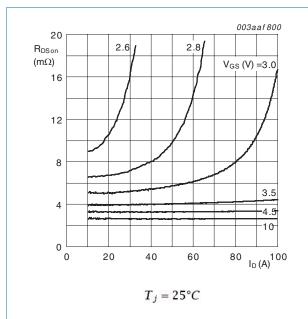


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

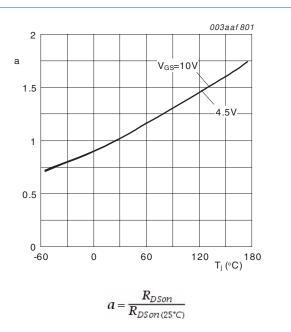


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

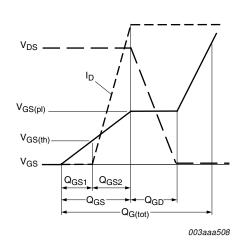


Fig 14. Gate charge waveform definitions

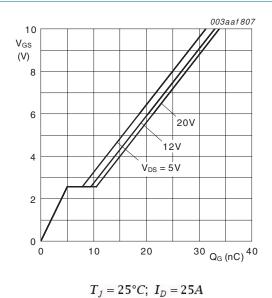


Fig 15. Gate-source voltage as a function of gate charge; typical values

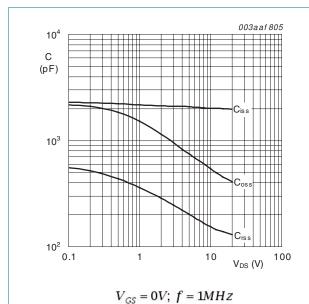


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

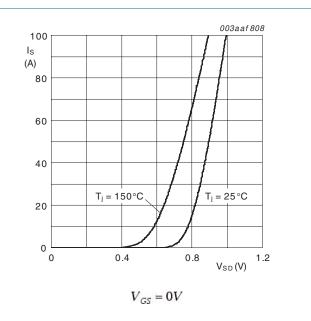


Fig 17. Source current as a function of source-drain voltage; typical values

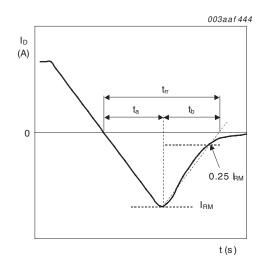


Fig 18. Reverse recovery timing definition

8. Package outline

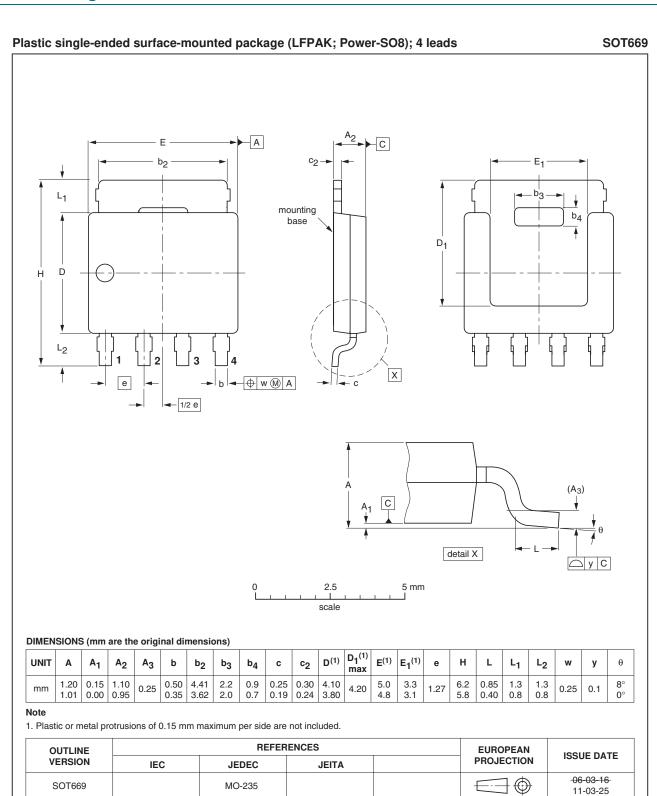


Fig 19. Package outline SOT669 (LFPAK; Power-SO8)

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Product data sheet

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Revision history

Table 8. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R9-25YLC v.1	20110502	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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